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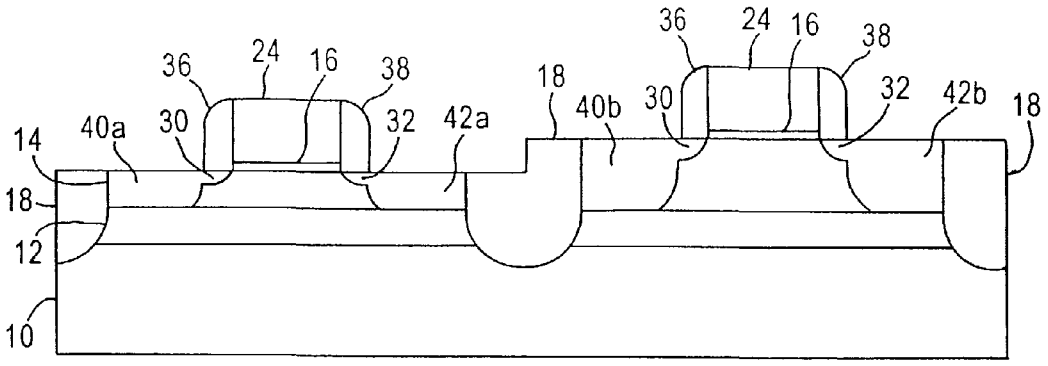
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(54) Title: SOI DEVICE WITH DIFFERENT SILICON THICKNESSES



(57) Abstract: A method of manufacturing a semiconductor device includes providing a silicon semiconductor layer (14) over an insulating layer (12), and partially removing a first portion of the silicon layer (14). The silicon layer (14) includes the first portion and a second portion, and a thickness of the second portion is greater than a thickness of the first portion. Initially, the first and second portions of the silicon layer (14) initially can have the same thickness. A semiconductor device is also disclosed.

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